

Product Overview

DARE22G OSC100M implements a current-capacitor relaxation oscillator for radiation-hardened applications in the commercial GF 22 nm FDSOI CMOS technology.

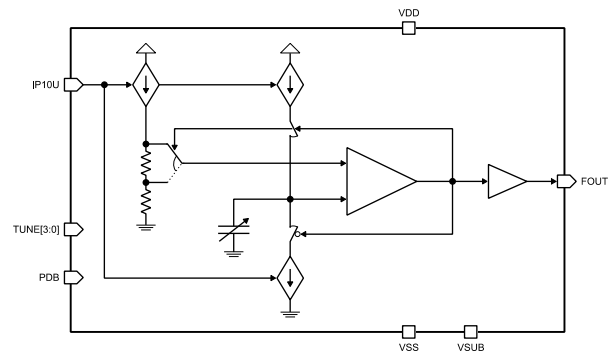
Features

DARE22G OSC100M main functionalities include:

- 100 MHz base output frequency ($\pm 4\%$)
- 4-bit trimming calibration
- 92 - 112 MHz output frequency range over corners after calibration
- Maximum SET-induced jitter of 2.8 ns
- Power-down mode ($< 1 \mu\text{A}$)
- Max current consumption lower than $250 \mu\text{A}$
- TID immunity over 100 krad (SiO_2)
- SET immunity over $60 \text{ MeV}\cdot\text{cm}^2/\text{mg}$
- SEL immunity over $70 \text{ MeV}\cdot\text{cm}^2/\text{mg}$

Block Diagram

The OSC100M macro cell mainly consists of a comparator and a tunable capacitor that is sequentially charged and discharged to produce an oscillating signal. Charge and discharge cycles are controlled by the comparator using voltage references generated internally through two resistors. A $10 \mu\text{A}$ sinking current signal provided via input IP10U is used as reference to voltage reference generation and charging/discharging circuits. This current can be provided by an instance of the DARE22G IVREF18 IP when it is co-integrated in the chip.



Pin Interface

Pin Name	Type	Description
VDD	Power	Power supply
VSS	Ground	Ground supply
VSUB	Ground	P-substrate bias voltage
IP10U	Analog	Reference current
PDB	Digital	Power-down enable
TUNE[3:0]	Digital	Frequency tuning bits
FOUT	Digital	Output clock

Physical Dimensions

DARE22G OSC100M is implemented as a core macro.

IP Name	Width	Height
OSC100M	68 μm	69 μm

Contact

For further information, please contact us at dare@imec.be

Operating Conditions

Performance and reliability are not guaranteed outside these recommended operating boundaries.

Parameter	Name	Minimum	Typical	Maximum	Unit
Supply voltage	VDD	0.72	0.8	0.88	V
Input reference current	I_{P10U}	9	10	11	μA
Operating temperature	T_j	-40	25	125	$^{\circ}\text{C}$
ESD rating (HBM)	V_{HBM}	2			kV
TID immunity	TID	100			krad (SiO_2)
SET hardening	SET_{th}	60			$\text{MeV}\cdot\text{cm}^2/\text{mg}$
SEL hardening	SEL_{th}	70			$\text{MeV}\cdot\text{cm}^2/\text{mg}$